ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESDM2032

The ESDM2032 is designed to protect voltage sensitive components that require low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

Features

- Low Clamping Voltage
- Small Body Outline Dimensions: 0.60 mm x 0.30 mm
- Low Body Height: 0.20 mmStand-off Voltage: 3.3 V
- IEC61000-4-2 Level 4 ESD Protection
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- µSD Card Protection
- Audio Line
- GPIO

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±30 ±30	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C Thermal Resistance, Junction-to-Ambient	P_D $R_{ hetaJA}$	313 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

ON

ON Semiconductor®

www.onsemi.com



MARKING DIAGRAM



X4DFN2 (0201) CASE 152AX



F = Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESDM2032MX4T5G	X4DFN2 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

See Application Note AND8308/D for further description of survivability specs.

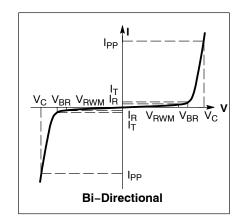
1

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

` ' '	•
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND	3.7		6.7	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			500	nA
Clamping Voltage TLP (Note 2)	V _C	IPP = 8 A SIEC 61000-4-2 Level 2 equivalent (±4 kV Contact, ±8 kV Air)		4.8		٧
		IPP = 16 A SEC 61000-4-2 Level 4 equivalent (±8 kV Contact, ±16 kV Air)		5.2		٧
Reverse Peak Pulse Current	I _{PP}	IEC61000-4-5 (8/20 μs)	15.5	16.5		Α
Clamping Voltage (8/20 μs) (Note 3)	V _C	I _{PP} = 15.5 A		5.8	8.2	٧
Dynamic Resistance	R _{DYN}	100 ns TLP Pulse		0.05		Ω
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz		18	23	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- ANSI/ESD STM5.5.1 Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 1 ns, averaging window; t₁ = 70 ns to t₂ = 90 ns.
 Non-repetitive current pulse at T_A = 25°C, per IEC61000-4-5 waveform.

TYPICAL CHARACTERISTICS

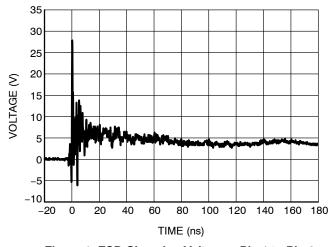


Figure 1. ESD Clamping Voltage - Pin 1 to Pin 2 8 kV Contact per IEC61000-4-2

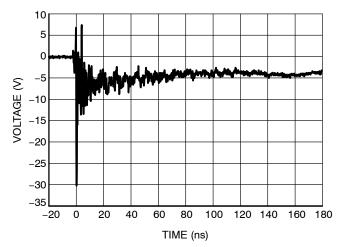
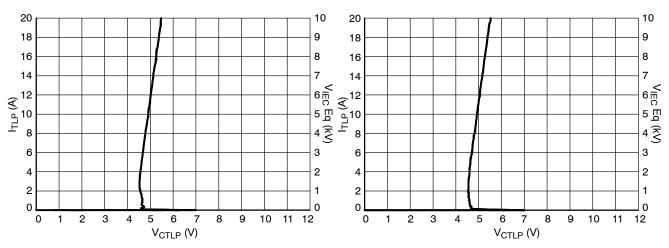


Figure 2. ESD Clamping Voltage - Pin 2 to Pin 1 8 kV Contact per IEC61000-4-2

TYPICAL CHARACTERISTICS



7

6

Figure 3. 100 ns TLP I-V Curve - Pin 1 to Pin 2

Figure 4. 100 ns TLP I-V Curve - Pin 2 to Pin 1

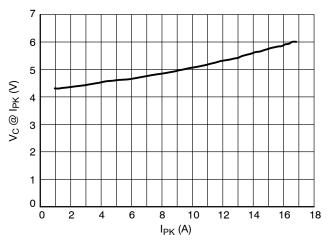
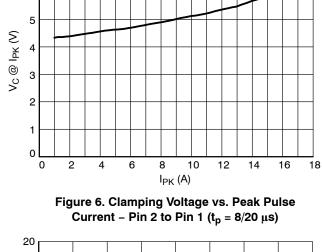
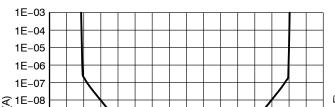


Figure 5. Clamping Voltage vs. Peak Pulse Current – Pin 1 to Pin 2 ($t_p = 8/20 \mu s$)



18 16 14 12 10 8 6 4 2 0 -3 2 -4 -2 -1 0 1



 $V_{R}(V)$ Figure 7. Reverse Leakage Current

-2

0

2

4

6

<u></u>4 1E-09

1E-10

1E-11

1E-12

1E-13

1E-14

-8

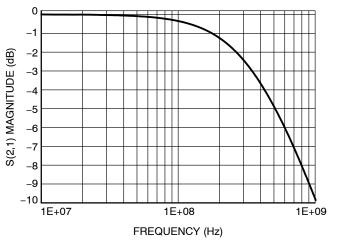
-6

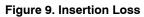
-4

3 V_{BIAS} (V) Figure 8. Line Capacitance, f = 1 MHz

8

TYPICAL CHARACTERISTICS





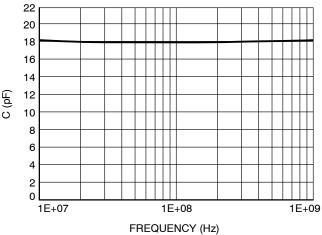


Figure 10. Capacitance Over Frequency

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

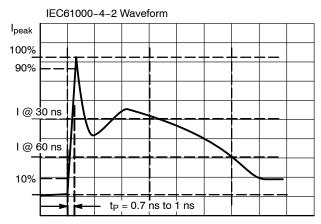


Figure 11. IEC61000-4-2 Spec

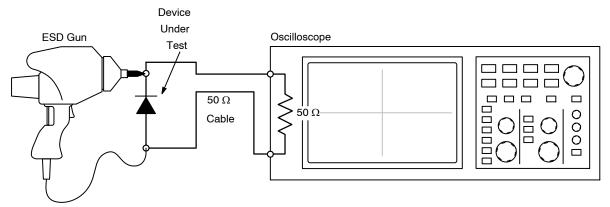


Figure 12. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

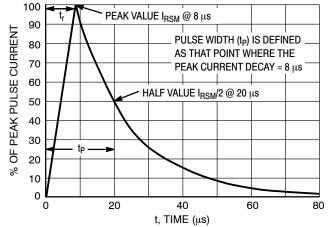


Figure 13. 8 x 20 μs Pulse Waveform

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 14. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 15 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

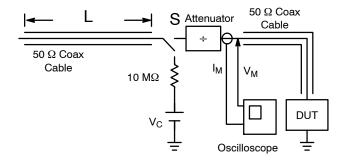


Figure 14. Simplified Schematic of a Typical TLP System

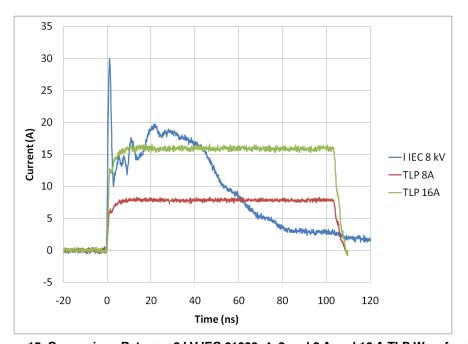
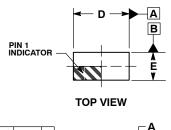


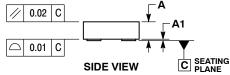
Figure 15. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

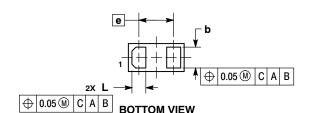


X4DFN2, 0.60x0.30, 0.36P CASE 152AX ISSUE G

DATE 12 APR 2019







- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.175	0.200	0.225	
A1	0.018 REF			
b	0.205	0.215	0.225	
D	0.575	0.600	0.625	
Е	0.275	0.300	0.325	
е	0.36 BSC			
L	0.145	0.155	0.165	

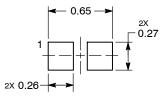
GENERIC MARKING DIAGRAM*



X = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON06808G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	X4DFN2, 0.60x0.30, 0.36P		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for ESD Suppressors / TVS Diodes category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

60KS200C D12V0H1U2WS-7 D18V0L1B2LP-7B 82356050220 D5V0M5U6V-7 NTE4902 P4KE27CA P6KE11CA P6KE39CA-TP
P6KE8.2A SA110CA SA60CA SA64CA SMBJ12CATR SMBJ8.0A SMLJ30CA-TP ESD101-B1-02ELS E6327 ESD112-B1-02EL E6327
ESD119B1W01005E6327XTSA1 ESD5V0J4-TP ESD5V0L1B02VH6327XTSA1 ESD7451N2T5G 19180-510 CPDT-5V0USP-HF
3.0SMCJ33CA-F 3.0SMCJ36A-F HSPC16701B02TP D3V3Q1B2DLP3-7 D55V0M1B2WS-7 DESD5V0U1BL-7B DRTR5V0U4SL-7
SCM1293A-04SO ESD200-B1-CSP0201 E6327 ESD203-B1-02EL E6327 SM12-7 SMF8.0A-TP SMLJ45CA-TP CEN955 W/DATA
82350120560 82356240030 VESD12A1A-HD1-GS08 CPDUR5V0R-HF CPDUR24V-HF CPDQC5V0U-HF CPDQC5V0USP-HF
CPDQC5V0-HF D1213A-01LP4-7B D1213A-02WL-7 ESDLIN1524BJ-HQ 5KP100A